

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

Email & Skype: info@chipsmall.com Web: www.chipsmall.com

Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China











30V Dual P-Channel MOSFET



SOP-8

Pin Definition:

5

1. Source 1 8. Drain 1 2. Gate 1 7. Drain 1 3. Source 2 6. Drain 2 4. Gate 2 5. Drain 2

PRODUCT SUMMARY

V _{DS} (V)	$R_{DS(on)}(m\Omega)$	I _D (A)
-30	25 @ V _{GS} = -10V	-7.1
	41 @ V _{GS} = -4.5V	-5.5

Features

- Advance Trench Process Technology
- High Density Cell Design for Ultra Low On-resistance

Application

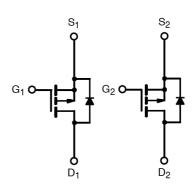
- Load Switches
- Notebook PCs
- Desktop PCs

Ordering Information

Part No.	Package	Packing
TSM4925DCS RLG	SOP-8	2.5Kpcs / 13" Reel

Note: "G" denotes for Halogen Free

Block Diagram



Dual P-Channel MOSFET

Absolute Maximum Rating (Ta = 25°C unless otherwise noted)

Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		V_{DS}	-30	V	
Gate-Source Voltage		V_{GS}	±20	V	
Continuous Drain Current		I _D	-7.1	Α	
Pulsed Drain Current		I _{DM}	-40	А	
Continuous Source Current (Diode C	onduction) ^{a,b}	I _S	-1.7	А	
Maximum Power Dissipation	Ta = 25°C	Б	2.0	W	
	Ta = 75°C	P_{D}	1.3		
Operating Junction Temperature	mperature T _J +		+150	°C	
Operating Junction and Storage Temperature Range		T_{J}, T_{STG}	- 55 to +150	°C	

Thermal Performance

Parameter	Symbol	Limit	Unit			
Junction to Case Thermal Resistance	R⊖ _{JC}	30	°C/W			
Junction to Ambient Thermal Resistance (PCB mounted)	ROJA	50	°C/W			

Notes:

- a. Pulse width limited by the Maximum junction temperature
- b. Surface Mounted on FR4 Board, $t \le 10$ sec.



30V Dual P-Channel MOSFET

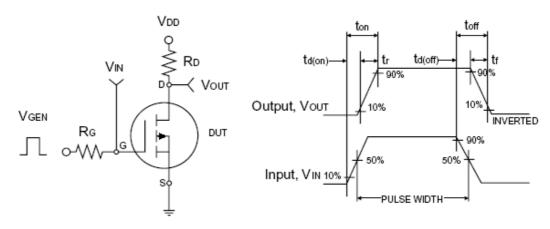


Electrical Specifications (Ta = 25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Тур	Max	Unit
Static						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = -250uA$	BV _{DSS}	-30			V
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	$V_{GS(TH)}$	-1		-3	V
Gate Body Leakage	$V_{GS} = \pm 20V, V_{DS} = 0V$	I _{GSS}			±100	nA
Zero Gate Voltage Drain Current	$V_{DS} = -30V, V_{GS} = 0V$	I _{DSS}			-1.0	μΑ
On-State Drain Current ^a	$V_{DS} = -5V, V_{GS} = -10V$	I _{D(ON)}	-40			Α
Drain-Source On-State Resistance	$V_{GS} = -10V, I_D = -7.1A$			20	25	mΩ
Drain-Source On-State Resistance	$V_{GS} = -4.5V, I_D = -5.5A$	$R_{DS(ON)}$		33	41	
Forward Transconductance ^a	$V_{DS} = -10V, I_{D} = -7.1A$	g _{fs}		24		S
Diode Forward Voltage	$I_S = -1.7A$, $V_{GS} = 0V$	V_{SD}		-0.8	-1.2	V
Dynamic ^b						
Total Gate Charge	$V_{DS} = -15V, I_{D} = -7.1A,$	Q_g		33	70	
Gate-Source Charge	$V_{DS} = -15V, I_D = -7.1A,$ $V_{GS} = -10V$	Q_gs		5.8		nC
Gate-Drain Charge	V _{GS} = -10 V	Q_gd		8.6		
Input Capacitance	\/ 45\/ \/ 6\/	C_{iss}		1573	1900	
Output Capacitance	$V_{DS} = -15V, V_{GS} = 0V,$ $f = 1.0MHz$	C _{oss}		319		pF
Reverse Transfer Capacitance	I = I.UIVIMZ	C_{rss}		211	295	
Switching ^c						
Turn-On Delay Time	V 45V D 450	t _{d(on)}		10	15	
Turn-On Rise Time	$V_{DD} = -15V, R_L = 15\Omega,$	t _r		15	25	~C
Turn-Off Delay Time	$I_D = -1A, V_{GEN} = -10V,$ $R_G = 6\Omega$	$t_{d(off)}$		110	170	nS
Turn-Off Fall Time	1 1C = 077	t _f		70	110	

Notes:

- a. pulse test: PW $\leq 300 \mu S$, duty cycle $\leq 2\%$ b. For DESIGN AID ONLY, not subject to production testing. b. Switching time is essentially independent of operating temperature.



Switching Test Circuit

Switchin Waveforms

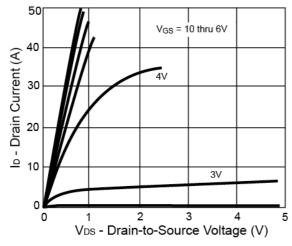


30V Dual P-Channel MOSFET

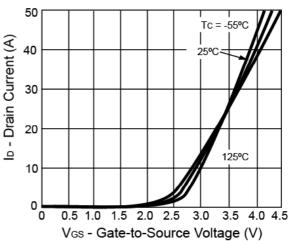
Pb RoHS

Electrical Characteristics Curve (Ta = 25°C, unless otherwise noted)

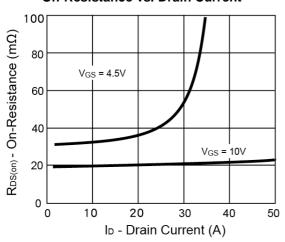




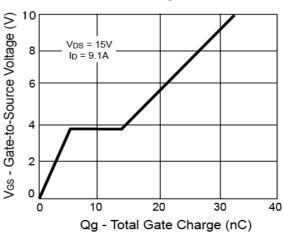
Transfer Characteristics



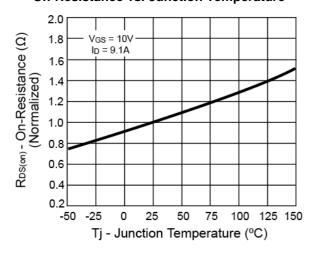
On-Resistance vs. Drain Current



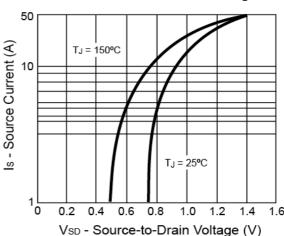
Gate Charge



On-Resistance vs. Junction Temperature



Source-Drain Diode Forward Voltage



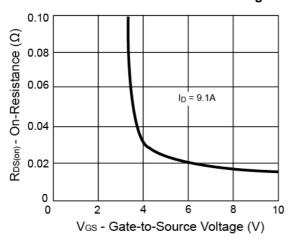


30V Dual P-Channel MOSFET

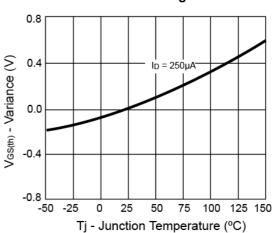


Electrical Characteristics Curve (Ta = 25°C, unless otherwise noted)

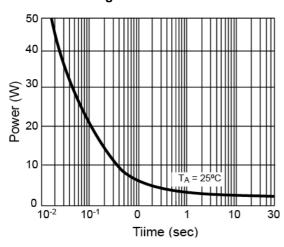
On-Resistance vs. Gate-Source Voltage



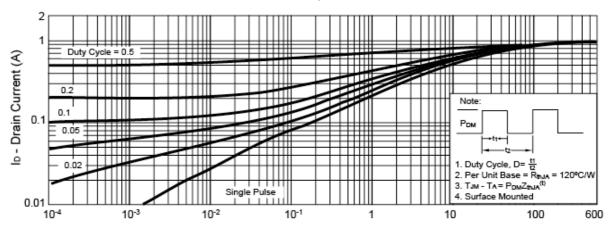
Threshold Voltage



Single Pulse Power



Normalized Thermal Transient Impedance, Junction-to-Ambient



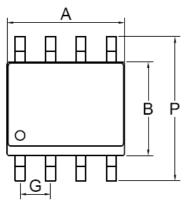
Square Wave Pulse Duration (sec)

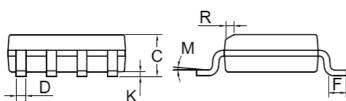






SOP-8 Mechanical Drawing





	SOP-8 DIMENSION					
DIM	MILLIMETERS		INCHES			
DIIVI	MIN	MAX	MIN	MAX.		
Α	4.80	5.00	0.189	0.196		
В	3.80	4.00	0.150	0.157		
С	1.35	1.75	0.054	0.068		
D	0.35	0.49	0.014	0.019		
F	0.40	1.25	0.016	0.049		
G	1.27BSC		0.05	BSC		
K	0.10	0.25	0.004	0.009		
М	0∘	7º	0∘	7º		
Р	5.80	6.20	0.229	0.244		
R	0.25	0.50	0.010	0.019		

Marking Diagram



Y = Year Code

M = Month Code for Halogen Free Product

 \mathbf{O} =Jan \mathbf{P} =Feb \mathbf{Q} =Mar \mathbf{R} =Apr

S =May T =Jun U =Jul V =Aug
W =Sep X =Oct Y =Nov Z =Dec

L = Lot Code



TSM4925D 30V Dual P-Channel MOSFET

Notice

Specifications of the products displayed herein are subject to change without notice. TSC or anyone on its behalf, assumes no responsibility or liability for any errors or inaccuracies.

Information contained herein is intended to provide a product description only. No license, express or implied, to any intellectual property rights is granted by this document. Except as provided in TSC's terms and conditions of sale for such products, TSC assumes no liability whatsoever, and disclaims any express or implied warranty, relating to sale and/or use of TSC products including liability or warranties relating to fitness for a particular purpose, merchantability, or infringement of any patent, copyright, or other intellectual property right.

The products shown herein are not designed for use in medical, life-saving, or life-sustaining applications. Customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify TSC for any damages resulting from such improper use or sale.